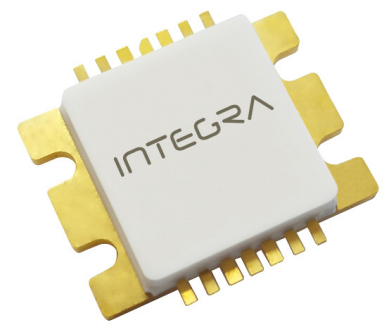


L-Band, GaN/SiC, RF Power Transistor

1030 and 1090 MHz | 225 W | 50% Efficiency | 37dB Gain | 50 V | 32µs Pulse Length, 4% Duty Cycle

IGT1011S150 is a high power, two-stage RF power transistor that has two discrete GaN-on-SiC transistors inside a single package. It has been designed to suit the unique needs of IFF/SSR avionics systems. It operates at both 1030 and 1090 MHz. Under 32µs pulse length, 4% duty cycle pulse conditions, it supplies a minimum of 150 W of peak output power, with typically >37 dB of gain. It operates from a 50 V supply voltage. For optimal thermal efficiency, the transistor is housed in a metal-based package with an epoxy-sealed ceramic lid.



FEATURES

- GaN on SiC HEMT Technology
- Output Power >150 W
- Fully matched to 50 Ω Impedance at the input and output
- High Efficiency - up to 50%
- 100% RF Tested
- RoHS and REACH Compliant

APPLICATIONS

- L-band Avionics IFF & SSR Systems
- Suitable for both uplink and downlink (Transponder/Interrogator)

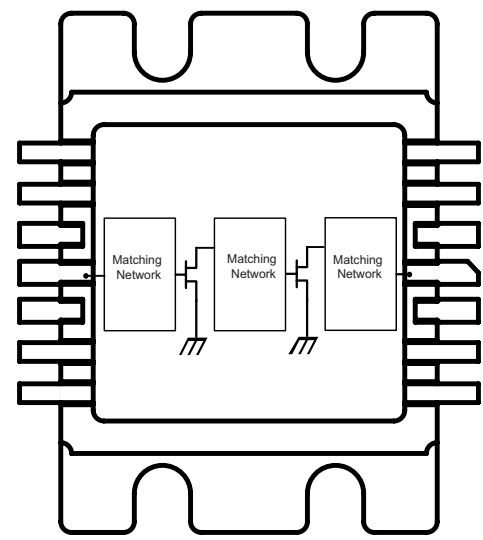


Table 1. RF Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Input Return Loss	IRL	7	15	25	dB	P _{OUT} = 150W f = 1030, 1090 MHz 32µs pulse length, 4% duty cycle V _{DS} = 50V, I _{DQ1} = 2mA, I _{DQ2} = 12mA
Gain	G	35	37	39	dB	
Drain Efficiency	η	40	45	50	%	
Pulse Droop	D	-0.4	-0.2	+0.2	dB	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	5:1				

Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V_{DS}	130	V	25 °C
DC Gate-Source Voltage	V_{GS}	-8 to +1.0	V	25 °C
DC Drain Current	I_D	10	A	25 °C
DC Gate Current for FET 1	I_G	2	mA	25 °C
DC Gate Current for FET 2	I_G	12.5	mA	25 °C
RF Input Power	$P_{RF,IN}$	0.6	W	25 °C
Operating Channel Temperature	T_{CH}	-55 to +225	°C	
Storage Temperature	T_{STG}	-55 to +150	°C	
Soldering Temperature	T_{SOLDER}	260 for 10s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V_P	-5.0			V	$V_{DS} = 50V, I_{DS} = 1mA$
Quiescent Gate Voltage	V_{Q1}		-2.5		V	$V_{DS} = 50V, I_{DS} = 2 mA$
Quiescent Gate Voltage	V_{Q2}		-2.7		V	$V_{DS} = 50V, I_{DS} = 12 mA$

Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	R_{TH}		0.3		°C/W	$P_{DISS} = 183W$ 32µs pulse length, 4% duty cycle $V_{DS} = 50V$

Table 5. Matching Network Source & Load Impedances (Case temperature = 25°C unless otherwise stated)

Frequency (MHz)	Z_{IF}	Z_{OF}	Units	Test Conditions
1030	50 + j0	50 + j0	Ω	$P_{OUT} = 150W$ 32µs pulse length, 4% duty cycle $V_{DS} = 50V, I_{DS1} = 2mA, I_{DS2} = 12mA$
1090	50 + j0	50 + j0	Ω	

TYPICAL PERFORMANCE

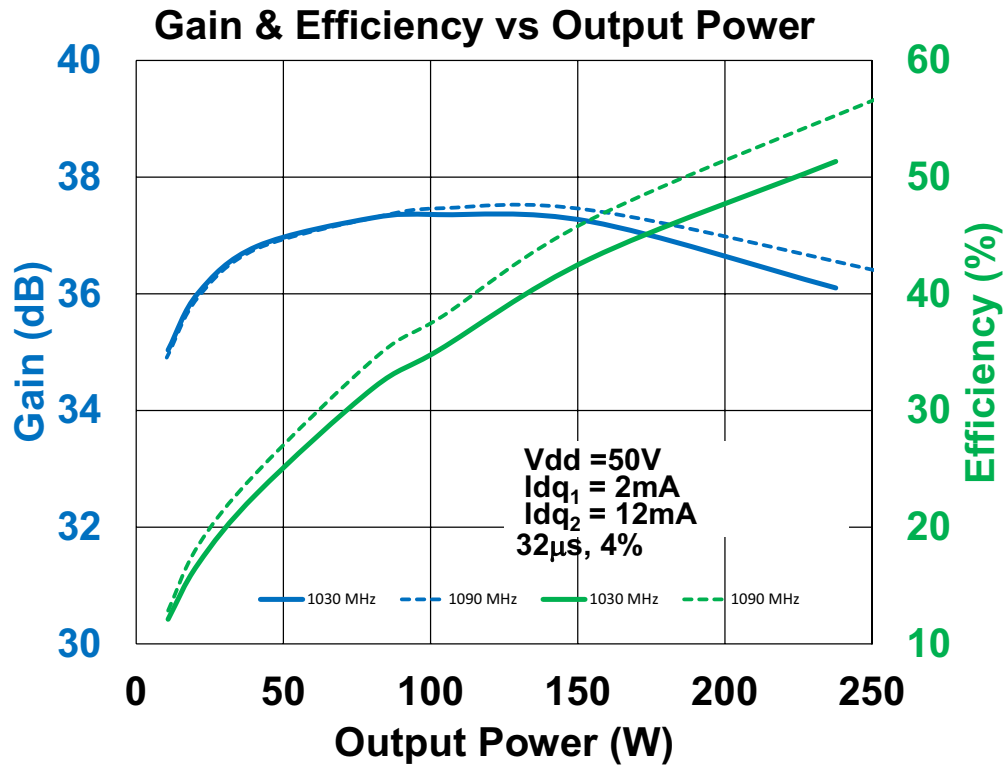
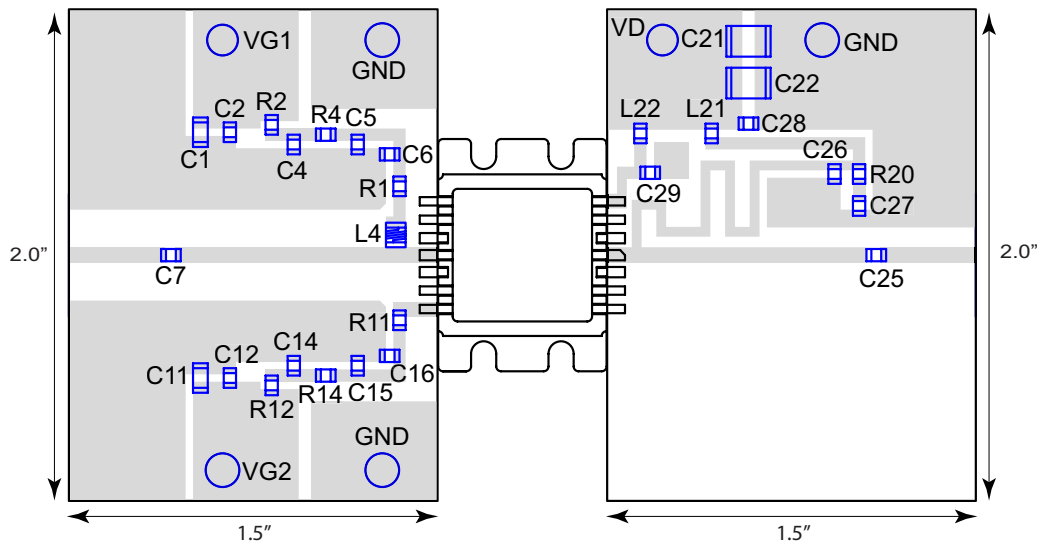


Figure 1

TEST FIXTURE

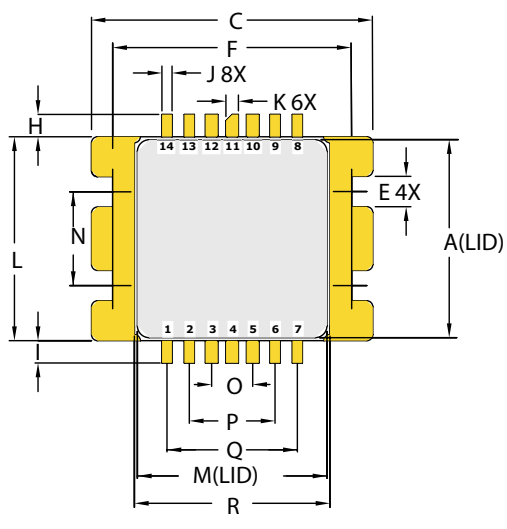


Note: it is recommended that a 4700 μ F 63V electrolytic capacitor be connected between ground and the positive supply terminal of the test fixture, and placed as close as possible to the test fixture, in order to minimise pulse droop.

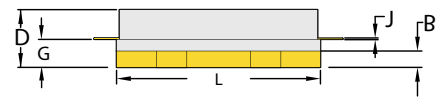
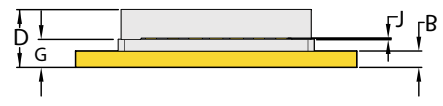
Bill of Materials for IGT1011S150 Test Fixture

Designator	Description	Part Number
C1, C11	CAP 1 μ F, 1206, 100V, X7R	12061C105K4T2A
C2, C5, C12, C15, C28	CAP 1000pF, 0805, 100V	08051A102J4T2A
C4, C14, C27	CAP 0.068pF, 250V, 0805, X7R	C0805C683KARAC#A
C6, C7, C16, C25, C26, C29	CAP 33pF, 0805, 250V	ATC600F330
C21, C22	CAP 1 μ F, 1812, 200V, X7R	18122C105KAT2A
L4	IND 39nH 1008	18122C105KAT2A
L21, L22	IND, FB, 38 OHM, 6A, 1206	Z1206C380BPWST
R1, R11, R20	RES, 5.1 OHM, 0805	CRCW08055R1JNEA
R2, R12	RES, 200 OHM, 0805	CRCW0805200RFKTA
R4, R14	RES, 0 OHM, 0805	CRCW08050000ZSTA
PC BOARD	RO4350B 0.030", 1oz/1oz Copper	

PACKAGE PFC77A1



DIM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	0.660	0.670	16.76	17.02
B	0.051	0.059	1.30	1.50
C	0.941	0.949	23.90	24.10
D	0.192	0.215	4.88	5.46
E	0.098	0.106	2.49	2.69
F	0.799	0.807	20.29	20.50
G	0.090	0.098	2.29	2.49
H	0.071	0.079	1.80	2.01
I	0.071	0.079	1.80	2.01
J	0.030	0.038	0.76	0.97
K	0.038	0.046	0.97	1.17
L	0.681	0.689	17.30	17.50
M	0.632	0.642	16.05	16.31
N	0.311	0.319	7.90	8.10
O	0.134	0.142	3.40	3.61
P	0.284	0.292	7.21	7.42
Q	0.434	0.442	11.02	11.23
R	0.653	0.661	16.59	16.79



PIN CONNECTIONS

1	Unused
2	Unused
3	Unused
4	RF IN + VG1
5	Unused
6	Unused
7	VG2
8	Unused
9	Unused
10	Unused
11	RF OUT + VD2
12	Unused
13	Unused
14	VD1

ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivity Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DEFINITIONS:

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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